

oxides and said insulator layer are formed of a same material.

40. (Amended) A semiconductor device comprising:  
a bulk silicon region comprising bulk silicon;  
a SiGe-on-insulator region comprising an insulator layer formed in said bulk silicon;  
a crystallized SiGe layer formed on said bulk silicon and said insulator layer by annealing a silicon germanium layer and having isolation trenches formed therein so as to remove defective regions; and  
isolation oxides formed in said isolation trenches.
41. (Amended) A hybrid bulk silicon and silicon-on-insulator (SOI) substrate, comprising:  
a bulk silicon layer;  
an insulator layer formed in said bulk silicon layer and having an upper surface which is substantially coplanar with an upper surface of said bulk silicon layer;  
a crystallized silicon layer formed on said bulk silicon layer and said insulator layer by annealing amorphous silicon and having isolation trenches formed therein so as to remove defective regions; and  
isolation oxides formed in said isolation trenches.
42. (Amended) The hybrid substrate according to claim 41, further comprising:  
a bulk silicon region comprising said bulk silicon layer and said crystallized silicon layer thereon; and  
a silicon-on insulator region comprising said insulator layer and said crystallized silicon layer thereon.

45. (Amended) A semiconductor device comprising:  
a bulk semiconductor region comprising bulk semiconductor;  
a semiconductor-on-insulator region comprising an insulator layer formed in said bulk semiconductor;  
a crystallized semiconductor layer formed on said insulator layer and said bulk

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semiconductor by annealing amorphous semiconductor and having isolation trenches formed therein so as to remove defective regions; and  
isolation oxides formed in said isolation trenches.

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